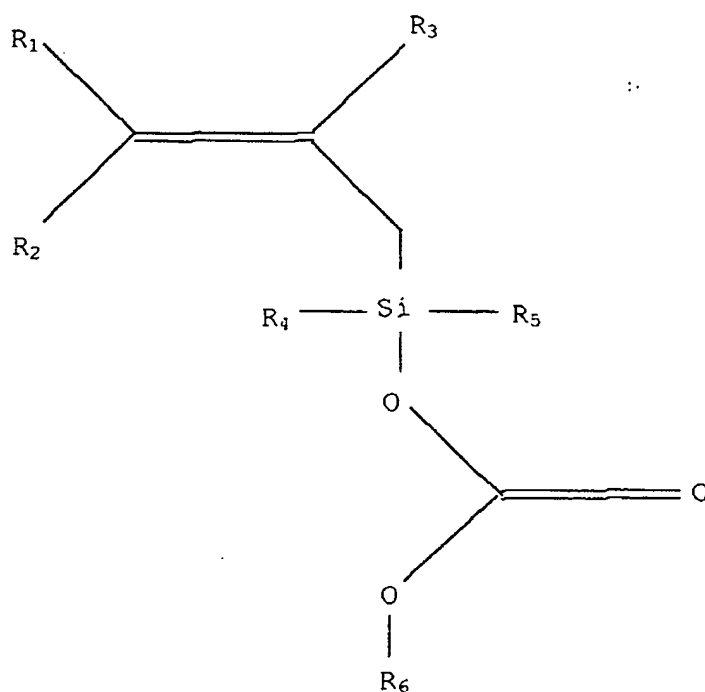


In the Claims:

1-13 (Canceled)

14. (New) A polymerizable composition for the production of a resist, comprising at least one unsaturated, polymerizable monomer having at least one silicon atom and at least one carbonyl group, a monomer of the general formula:



wherein:

R₁, is selected from the group consisting of H and alkyl radicals;

R₂, is selected from the group consisting of H and alkyl radicals;

R₃ is selected from the group consisting of H and alkyl radicals;

R₄ comprises alkyl radicals and/or a silicon-containing compound;

R₅ comprises alkyl radicals and/or a silicon-containing compound;

R₆ comprises alkyl radicals; and

wherein R₁, R₂, R₃, R₄, R₅, and R₆ are either identical or different from one another.

15. (New) The polymerizable composition as claimed in claim 14 wherein at least one of R₁, R₂, R₃ comprises a methyl radical.

16. (New) The polymerizable composition as claimed in claim 14 wherein at least one of R₄ and R₅ comprises a methyl radical or siloxane.

17. (New) The polymerizable composition as claimed in claim 14 wherein R₆ comprises a tert-butyl radical.

18. (New) The polymerizable composition as claimed in claim 14, wherein at least one alkyl radical has a chain length of C₁ to C₈.

19. (New) A polymer prepared by polymerization of at least the composition as claimed in claim 14.

20. (New) A resist comprising:

a content of from 2 to 30% of polymer prepared by polymerization of a composition as claimed in claim 14;

a content of from 70 to 98% of solvent; and

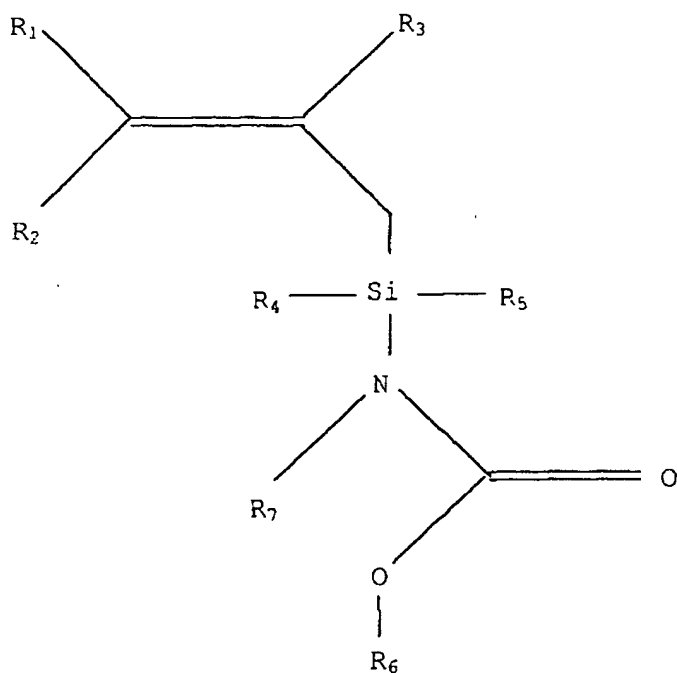
a content of from 0.1 to 10% of photo acid generator.

21. (New) The resist as claimed in claim 20, wherein the solvent comprises at least one of methoxypropyl acetate, ethyl acetate, ethyl lactate, cyclohexanone, gamma-butyrolactone and methyl ethyl ketone.

22. (New) The resist as claimed in claim 20, wherein the photo acid generator comprises at least one of Crivello salt, diphenylsulfonium sulfonate, diphenyliodonium sulfate, phthalimidosulfonate and ortho-nitrobenzylsulfonate.

23. (New) A lithography process for the production of a structure on a substrate, the process comprising coating the substrate with a resist as claimed in claim 20.

24. (New) A polymerizable composition for the production of a resist, comprising at least one unsaturated, polymerizable monomer having at least one silicon atom and at least one carbonyl group, the monomer being represented by the formula:



wherein:

R₁, is selected from the group consisting of H and alkyl radicals;

R₂, is selected from the group consisting of H and alkyl radicals;

R₃ is selected from the group consisting of H and alkyl radicals;

R₄ comprises an alkyl radical and/or a silicon-containing compound;

R₅ comprises an alkyl radical and/or a silicon-containing compound;

R₆ comprises an alkyl radical;

R₇ is selected from the group consisting of H and alkyl radicals;

wherein R₁, R₂, R₃, R₄, R₅, R₆, and R₇ are either identical or different from one another.

25. (New) The polymerizable composition as claimed in claim 24 wherein at least one of R₁, R₂, R₃ comprises a methyl radical.

26. (New) The polymerizable composition as claimed in claim 24 wherein at least one of R₄ and R₅ comprises a methyl radical or siloxane.

27. (New) The polymerizable composition as claimed in claim 24 wherein R₆ comprises a tert-butyl radical.

28. (New) The polymerizable composition as claimed in claim 24, wherein at least one alkyl radical has a chain length of C₁ to C₈.

29. (New) A polymer prepared by polymerization of the composition as claimed in claim 24.

30. (New) A resist comprising:
- a content of from 2 to 30% of polymer prepared by polymerization of a composition as claimed in claim 24;
 - a content of from 70 to 98% of solvent; and
 - a content of from 0.1 to 10% of photo acid generator.
31. (New) The resist as claimed in claim 30, wherein the solvent comprises at least one of methoxypropyl acetate, ethyl acetate, ethyl lactate, cyclohexanone, gamma-butyrolactone and methyl ethyl ketone.
32. (New) The resist as claimed in claim 30, wherein the photo acid generator comprises at least one of Crivello salt, diphenylsulfonium sulfonate, diphenyliodonium sulfate, phthalimidosulfonate and ortho-nitrobenzylsulfonate.
33. A lithography process for the production of a structure on a substrate, the process comprising coating the substrate with a resist as claimed in claim 30.